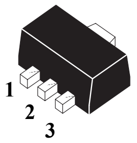
WEITRON

KTA1664

PNP Epitaxial Planar Transistors

Lead(Pb)-Free

1. BASE
2. COLLECTOR
3. EMITTER



SOT-89

ABSOLUTE MAXIMUM RATINGS (T_A=25˚C)

Rating	Symbol	Limits	Unit
Collector-Base Voltage	V_{CBO}	-35	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-0.8	A
Collector Power Dissipation	P_D	0.5	W
Junction Temperature	T_j	-55 to +150	˚C
Storage Temperature Range	T_{stg}	-55 to +150	˚C

ELECTRICAL CHARACTERISTICS(T_A=25˚C unless otherwise noted)

Parameter	Symbol	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage I_C=-1mA, I_E=0	BV_{CBO}	-35	-	-	V
Collector-Emitter Breakdown Voltage I_C=-10mA, I_B=0	BV_{CEO}	-30	-	-	V
Emitter-Base Breakdown Voltage I_E=-1mA, I_C =0	BV_{EBO}	-5	-	-	V
Collector Cutoff Current V_{CB}=-35V, I_E=0	I_{CBO}	-	-	-0.1	μA
Collector Cutoff Current V_{EB}=-5V, I_C=0	I_{EBO}	-	-	-0.1	μA

ELECTRICAL CHARACTERISTICS (T_A=25°C Unless otherwise noted)

ON CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
DC Current Gain V_{CE}=-1V, I_C=-100mA	h_{FE}	100	-	320	-
DC Current Gain V_{CE}=-1V, I_C=-700mA	h_{FE}	35	-	-	-
Collector-Emitter Saturation Voltage I_C=-1.5A, I_B=-30mA	$V_{CE(sat)}$	-	-	-0.7	V
Base-Emitter Voltage V_{CE}=-1V, I_C=-10mA	V_{BE}	-0.5	-	-0.8	V

DYNAMIC CHARACTERISTICS

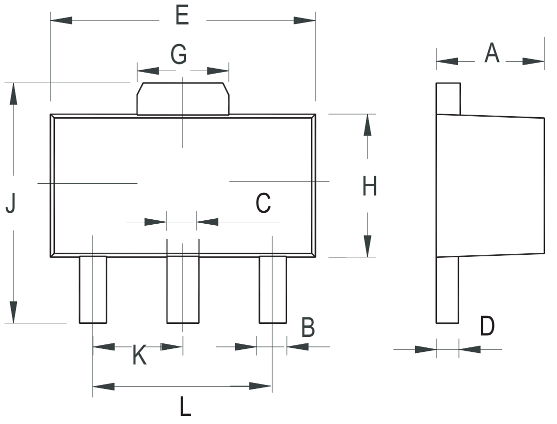
Characteristic	Symbol	Min	Typ	Max	Unit
Transition Frequency V_{CE}=-5V, I_C=-10mA	f_T	-	120	-	MHz
Output Capacitance V_{CB}=-10V, I_E=0, f=1MHz	C_{ob}	-	19	-	pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320
Marking	RO	RY

SOT-89 Outline Dimensions

unit:mm



SOT-89		
Dim	**Min**	**Max**
A	1.400	1.600
B	0.320	0.520
C	0.360	0.560
D	0.350	0.440
E	4.400	4.600
G	1.400	1.800
H	2.300	2.600
J	3.940	4.250
K	1.500 TYP	
L	2.900	3.100